

ABSTRACT

Method and structure for forming strained devices

A method for manufacturing a device includes mapping extreme vertical boundary conditions of a mask layer based on vertical edges of a deposited first layer (120) and a second layer (124). The mask layer (126) is deposited over portions of the second layer (124) based on the mapping step. The exposed area of the second layer (124) is etched to form a smooth boundary between the first layer (120) and the second layer (124). The resist layer (124) is stripped. The resulting device is an improved PFET device and NFET device with a smooth boundary between the first and second layers such that a contact can be formed at the smooth boundary without over etching other areas of the device.

Fig. 14.



162162
G00002

